

R-C Thermal Model Parameters

DESCRIPTION

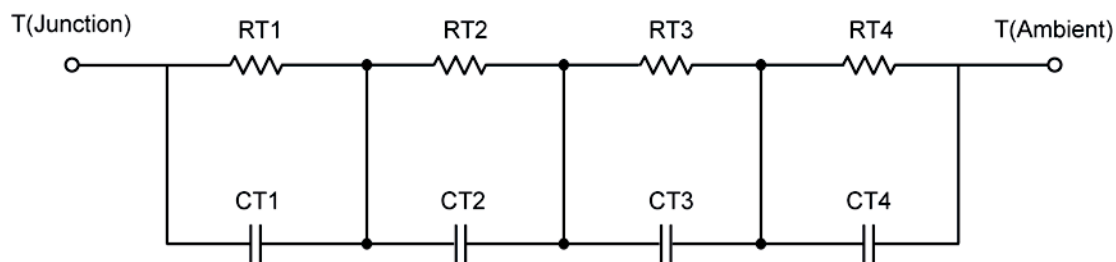
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

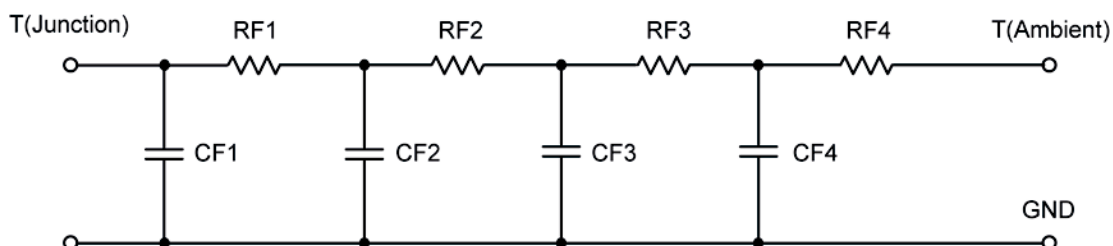
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	7.9474	N/A	3.9539
RT2	13.8948	N/A	3.0190
RT3	37.4396	N/A	16.9043
RT4	50.5626	N/A	15.0020
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.2868 m	N/A	8.3834 m
CT2	69.9427 m	N/A	308.0764 μ
CT3	8.3291 m	N/A	14.4734 m
CT4	1.2354	N/A	4.1561 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	14.0037	N/A	4.7053
RF2	27.6645	N/A	13.9834
RF3	17.8069	N/A	13.7406
RF4	50.4668	N/A	6.5571
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	1.6258 m	N/A	433.9929 u
CF2	6.3373 m	N/A	2.1524 m
CF3	15.0498 m	N/A	626.8923 u
CF4	1.1715	N/A	48.0595 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

